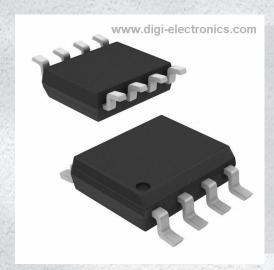


# **FAN7527BM Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number FAN7527BM-DG

Manufacturer onsemi

Manufacturer Product Number FAN7527BM

Description IC PFC CTRLR TRANSITION 8SOP

Detailed Description PFC IC Discontinuous (Transition) 8-SOIC



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



### **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
FAN7527BM	onsemi
Series:	Product Status:
	Obsolete
Mode:	Frequency - Switching:
Discontinuous (Transition)	
Current - Startup:	Voltage - Supply:
60 μA	11.5V ~ 30V
Operating Temperature:	Mounting Type:
-25°C ~ 125°C	Surface Mount
Package / Case:	Supplier Device Package:
8-SOIC (0.154", 3.90mm Width)	8-SOIC
Base Product Number:	
FAN7527	

### **Environmental & Export classification**

	22.00.00
Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8542.39.0001



### **Power Factor Correction** Controller

### **FAN7527B**

#### Description

The FAN7527B provides simple and high-performance active Power Factor Correction (PFC). The FAN7527B is optimized for electronic ballasts and low-power, high-density power supplies that require minimum board size, reduced external components, and low power dissipation. Because the R/C filter is included in the current-sense block, an external R/C filter is not necessary. Special circuitry prevents no-load runaway conditions. Regardless of the supply voltage, the output drive clamping circuit limits the overshoot of the power MOSFET gate drive, which improves system reliability.

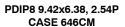
#### **Features**

- Internal Startup Timer
- Internal R/C Filter Eliminates the Need for External R/C Filter
- Precise Adjustable Output Over-Voltage Protection
- Zero Current Detector
- One Quadrant Multiplier
- Trimmed 1.5% Internal Band Gap Reference
- Under-Voltage Lockout with 3 V of Hysteresis
- Totem-Pole Output with High-State Clamp

- 8-Pin SOP or 8-Pin DIP
   These Devices are Pb-Free and are RoHS Compliant

  Applications
   Electronic Ballast
   SMPS

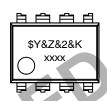


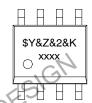




SOIC8 CASE 751EB

#### MARKING DIAGRAM





onsemi Logo 87 = Assembly Plant Code &2 = 2-Digit Date Code Lot Run Traceability Code &K XXXX Specific Device Code

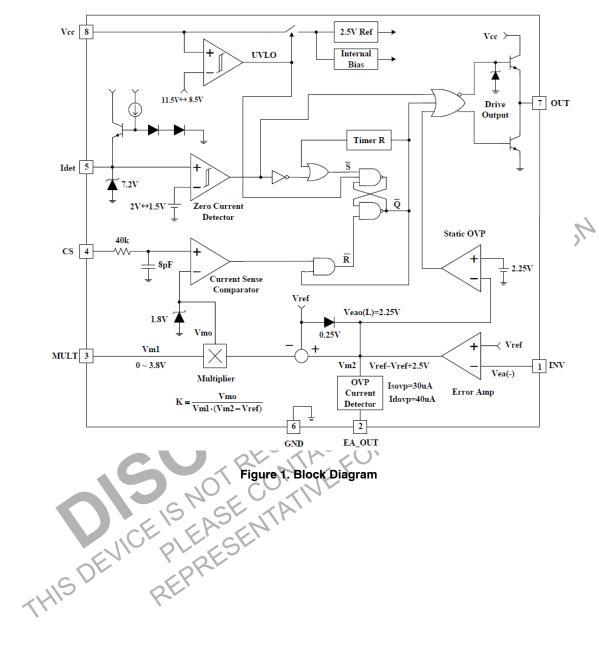
#### ORDERING INFORMATION

7	Device	Package	Shipping <sup>†</sup>
	FAN7527BN	PDIP8 (Pb-Free)	3000 / Tube
2	FAN7527BMX	SOIC8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NOTE: Operating Temperature Range of both devices is -25 to +125°C

#### **BLOCK DIAGRAM**



#### **PIN CONFIGURATION**

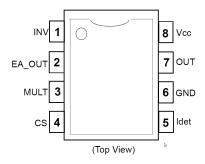


Figure 2. Pin Configuration

#### **PIN DEFINITIONS**

Pin #	Name	Description
1	INV	Inverting input of the error amplifier. The output of the boost converter should be resistively divided to 2.5 V and connected to this pin.
2	EA_OUT	Output of the error amplifier. Feedback compensation network is placed between this pin and the INV pin.
3	MULT	Input to the multiplier stage. The full-wave rectified AC voltage is divided to less than 2 V and is connected to this pin.
4	CS	Input of the PWM comparator. The MOSFET current is sensed by a resistor and the resulting voltage is applied to this pin. An internal R/C filter is included to reject high-frequency noise
5	ldet	Zero Current Detection (ZCD) input
6	GND	Ground
7	OUT	Gate driver output. Push-pull output stage is able to drive the power MOSFET with a peak current of 500 mA
8	V <sub>CC</sub>	Supply voltage of driver and control circuits
THIS	DEVICE	of 500 mA  Supply voltage of driver and control circuits

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter			Max.	Unit
Vcc	Supply Voltage	Supply Voltage		30	V
Iон, IoL	Peak Drive Output Current			±500	mA
ICLAMP	Driver Output Clamping Diodes V <sub>O</sub> > V <sub>CC</sub> or	V <sub>O</sub> < -0.3 V		±10	mA
IDET	Detector Clamping Diodes			±10	mA
Vin	Error Amplifier Multiplier and Comparator Input Voltages		-0.3	6.0	V
TJ	Operation Junction Temperature			+150	°C
Topr	Operating Temperature Range		-25	+125	°C
Tstg	Storage Temperature Range		-65	+150	°C
Б	Power Dissipation	SOIC8		0.8	W
P <sub>D</sub>		PDIP8		1.1	W
ΘЈΑ	Thermal Resistance Junction-Ambient	SOIC8		150	°C/W
ØJA		PDIP8	-6	110	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **TEMPERATURE CHARACTERISTICS**

 $(-25^{\circ}\text{C} \le \text{T}_{\text{A}} \le 125^{\circ}\text{C})$ 

Symbol	Parameter Min.	Тур.	Max.	Unit
$\Delta V$ REF	Temperature Stability Reference Voltage (V <sub>REF</sub> )	20		mV
ΔΚ/ΔΤ	Temperature Stability for Multiplier Gain (K)	-0.2		% / °C
TH	S DEVICE IS NOT RECONTACT OR INFO REPRESENTATIVE POR INFO			

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{CC} = 14 \text{ V}, -25^{\circ}\text{C} \le T_{A} \le 125^{\circ}\text{C}, \text{ unless otherwise stated.})$ 

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
UNDER-VOL	TAGE LOCKOUT		_	=		
Vth(st)	Start Threshold Voltage	V <sub>CC</sub> Increasing	10.5	11.5	12.5	V
HY(st)	UVLO Hysteresis		2	3	4	٧
SUPPLY CUR	RENT SECTION					
lsт	Startup Supply Current	$V_{CC} = V_{th(st)} - 0.2 \text{ V}$	10	60	100	μΑ
Icc	Operating Supply Current	Output Not Switching		3	6	mA
ICC(OVP)	Operating Current at OVP	V <sub>INV</sub> = 3 V		1.7	4.0	mA
IDCC	Dynamic Operating Supply Current	50 kHz, C <sub>l</sub> = 1 nF		4	8	mA
ERROR AMP	LIFIER SECTION				4	
VREF	Voltage Feedback Input Threshold	I <sub>REF</sub> = 0 mA, T <sub>A</sub> = 25°C	2.465	2.500	2.535	V
		25°C ≤ T <sub>A</sub> ≤ 125°C	2.440	2.500	2,560	
ΔVFEF1	Line Regulation	14 V ≤ V <sub>CC</sub> ≤ 25 V		0.1	10.0	mV
$\Delta V$ FEF3	Temperature Stability of V <sub>REF</sub> (Note 1)	$-25^{\circ}\text{C} \le \text{T}_{\text{A}} \le 125^{\circ}\text{C}$		20		mV
lb(ea)	Input Bias Current		-0.5		0.5	μΑ
Isource	Output Source Current	V <sub>M2</sub> = 4 V	-2	-4		mA
Isink	Output Sink Current	V <sub>M2</sub> = 4 V	2	4		mA
VEAO(H)	Output Upper Clamp Voltage (Note 1)	I <sub>SOURCE</sub> = 0.1 mA	RIVI	6		<b>V</b>
VEAO(L)	Output Lower Clamp Voltage (Note 1)	I <sub>SINK</sub> = 0.1 mA	.0.	2.25		<b>V</b>
G <sub>V</sub>	Large Signal Open-Loop Gain (Note 1)	0,0	60	80		dB
PSRR	Power Supply Rejection Ratio (Note 1)	14 V ≤ V <sub>CC</sub> ≤ 25 V	60	80		dB
GBW	Unity Gain Bandwidth (Note 1)	JUE.		1		MHz
SR	Slew Rate (Note 1)			0.6		V/μs
MULTIPLIER	SECTION	,				
lb(m)	Input Bias Current (Pin 3)		-0.5		0.5	μΑ
$\Delta V_{M1}$	M1 Input Voltage Range (Pin 3)				3.8	V
ΔV <sub>M2</sub>	M2 Input Voltage Range (Pin 2)		VREF		V <sub>REF</sub> +2.5	V
К	Multiplier Gain (Note 1)	V <sub>M1</sub> = 1 V, V <sub>M2</sub> = 3.5 V	0.36	0.44	0.52	1 / V
VOMAX(m)	Maximum Multiplier Output Voltage	V <sub>INV</sub> = 0 V, V <sub>M1</sub> = 4 V	1.65	1.80	1.95	V
ΔΚ/ΔΤ	Temperature Stability of K (Note 1)	$-25^{\circ}\text{C} \le \text{T}_{\text{A}} \le 125^{\circ}\text{C}$		-0.2		% / °C
CURRENT SE	ENSE SECTION	_				
VIO(CS)	Input Offset Voltage (Note 1)	$V_{M1} = 0 \text{ V}, V_{M2} = 2.2 \text{ V}$	-10	3	10	mV
lb(CS)	Input Bias Current	0 V ≤ V <sub>CS</sub> ≤ 1.7 V	-1.0	-0.1	1.0	μΑ
tD(CS)	Current Sense Delay to Output (Note 1)			200	500	ns
ZERO CURRI	ENT DETECT SECTION	_			,	1
VTH(DET)	Input Voltage Threshold	V <sub>DET</sub> Increasing	1.7	2.0	2.3	V
HY(DET)	Detect Hysteresis		0.2	0.5	0.8	V
VCLAMP(I)	Input Low Clamp Voltage	I <sub>DET</sub> = -100 μA	0.45	0.75	1.00	V
VCLAMP(H)	Input High Clamp Voltage	I <sub>DET</sub> = 3 mA	6.5	7.2	7.9	V

#### **ELECTRICAL CHARACTERISTICS** (continued)

 $(V_{CC} = 14 \text{ V}, -25^{\circ}\text{C} \le T_{A} \le 125^{\circ}\text{C}, \text{ unless otherwise stated.})$ 

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ZERO CURRE	ENT DETECT SECTION					
lb(DET)	Input Bias Current	1 V ≤ V <sub>DET</sub> ≤ 5 V	-1.0	-0.1	1.0	μΑ
ICLAMP(D)	Input High/Low Clamp Diode Current (Note 1)				±3	mA
OUTPUT SEC	CTION					
Vон	Output Voltage High	I <sub>O</sub> = -10 mA	10.5	11.0		<b>V</b>
Vol	Output Voltage Low	I <sub>O</sub> = 10 mA		0.8	1.0	>
t <sub>R</sub>	Rising Time (Note 1)	C <sub>L</sub> = 1 nF		130	200	ns
t <sub>F</sub>	Falling Time (Note 1)	C <sub>L</sub> = 1 nF		50	120	ns
VOMAX(O)	Maximum Output Voltage	$V_{CC} = 20 \text{ V}, I_{O} = 100 \mu\text{A}$	12	14	16	V
VOMIN(O)	Output Voltage with UVLO Activated	$V_{CC} = 5 \text{ V}, I_{O} = 100 \mu\text{A}$			1, 1/	V
RESTART TIM	MER SECTION				. CIO.	
tD(RST)	Restart Time Delay	V <sub>M1</sub> = 1 V, V <sub>M2</sub> = 3.5 V		150		μs
OVER-VOLTA	AGE PROTECTION SECTION			N		
Isovp	Soft OVP Detecting Current		25	30	35	μΑ
IDOVP	Dynamic OVP Detecting Current		35	40	45	μΑ
Vovp	Static OVP Threshold Voltage	V <sub>INV</sub> = 2.7 V	2.10	2.25	2.40	V
Product param performance m 1. These para Multiplier G $K = \frac{Pir}{V_{M1}}$ where $V_{M1}$	Dynamic OVP Detecting Current  Static OVP Threshold Voltage  letric performance is indicated in the Electrical Characterist meters, although guaranteed, are not 100% tested in:  14_Threshold    V <sub>M2</sub> - V <sub>REF</sub>	variate ristics for the listed testics if operated under different ded in production.	onditions.	, uniess oth	erwise noted	a. Produc

$$K = \frac{Pin4\_Threshold}{V_{M1} \times (V_{M2} - V_{REF})}$$

#### **TYPICAL PERFORMANCE CHARACTERISTICS**

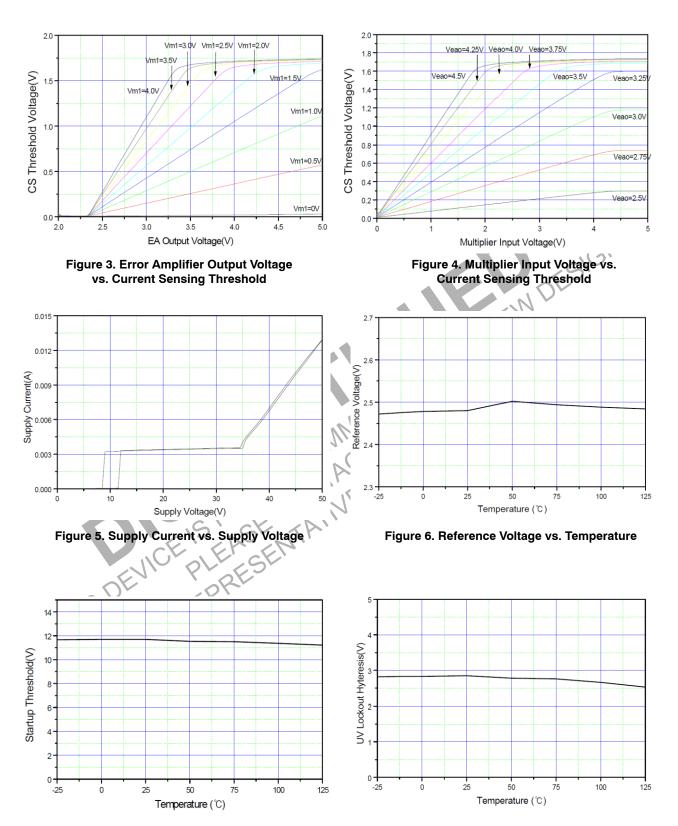
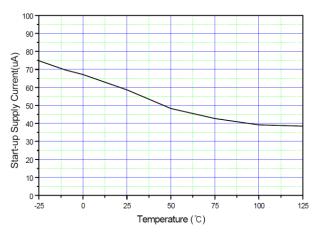


Figure 7. Startup Threshold vs. Temperature

Figure 8. UVLO Hysteresis vs. Temperature

#### TYPICAL PERFORMANCE CHARACTERISTICS (continued)



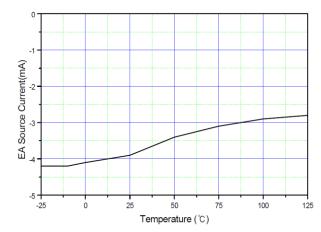
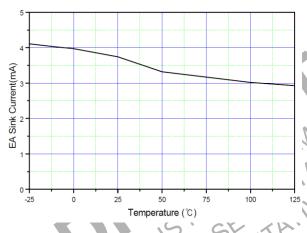


Figure 9. Startup Supply Current vs. Temperature

Figure 10. Error Amplifier Source Current



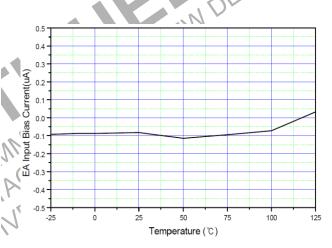
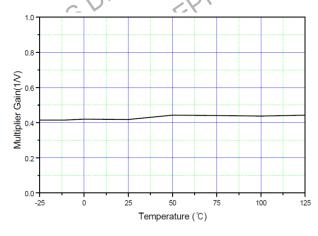


Figure 11. Error Amplifier Sink Current vs.
Temperature

Figure 12. Error Amplifier Input Bias Current vs. Temperature



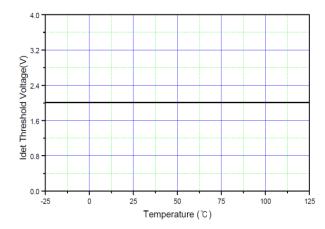
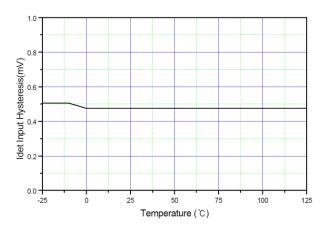


Figure 13. Multiplier Gain vs. Temperature

Figure 14. I<sub>DET</sub> Threshold Voltage vs. Temperature

#### TYPICAL PERFORMANCE CHARACTERISTICS (continued)



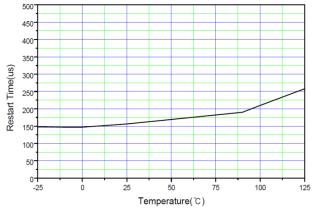
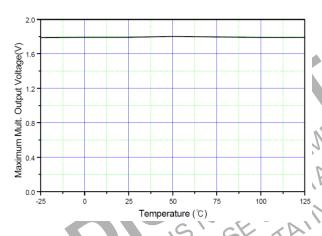


Figure 15. IDET Input Hysteresis vs. Temperature

Figure 16. Restart Time vs. Temperature



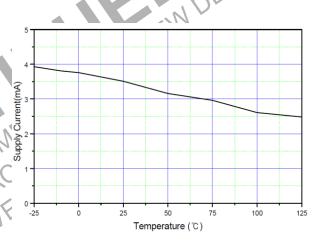


Figure 17. Maximum Multiplier Output Voltage vs. Temperature

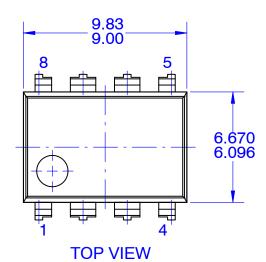
Figure 18. Supply Current vs. Temperature

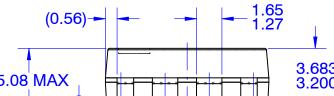


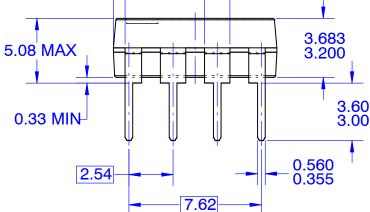
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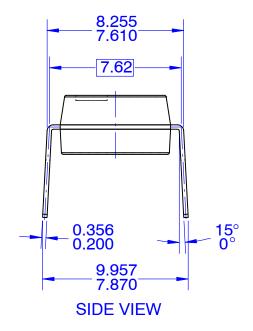
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**FRONT VIEW** 



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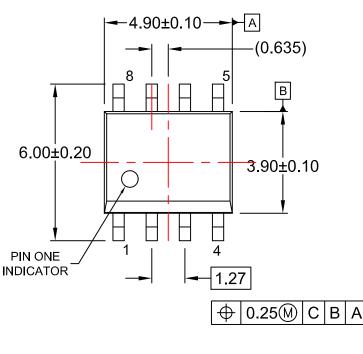
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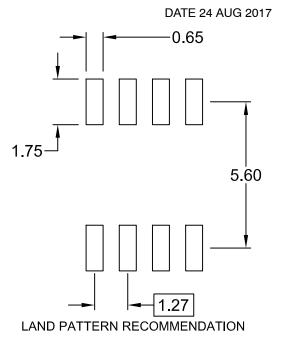
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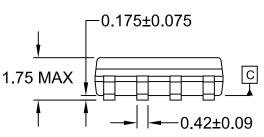


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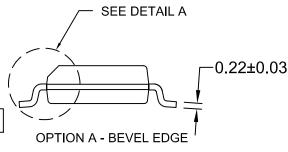
#### SOIC8 CASE 751EB ISSUE A

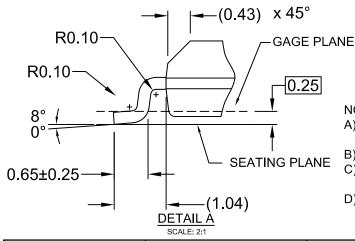














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